NEWS RELEASE

TagoreTech to Participate in IMS 2025

Chicago, IL, USA and Kolkata, India – June 5, 2025 – TagoreTech Inc., a leader in disruptive semiconductor solutions for over 14 years, announces its participation in the International Microwave Symposium (IMS) 2025.

At the in-person event held at the Moscone Center in San Francisco, CA, TagoreTech will showcase its latest innovations, including Gallium Arsenide (GaAs) Low Noise Amplifiers (LNAs), resilient Low Noise Amplifiers, Second-Generation Gallium Nitride (GaN)-based RF switches, MCM switch-LNA modules, and GaN Power Amplifier devices. Visit TagoreTech at **booth #332.**

"TagoreTech continues to push boundaries in RF performance with practical, scalable solutions that address real design challenges," said **Paul Hart, CEO and President of TagoreTech**. "Our work in GaN and wide bandgap technologies aligns with IMS mission of driving technical innovation in high-reliability, high-frequency applications."

"IMS is the premier stage for RF and microwave innovation, and we're excited to showcase how our latest GaAs LNAs, GaN switches, and integrated modules deliver real performance and integration benefits," said **Klaus Buehring, Chief Marketing Officer at TagoreTech**. "Our focus remains on helping customers reduce system complexity and power consumption while accelerating time-to-market across infrastructure, defense, and emerging wireless applications."

"Our second-generation GaN RF switches and hybrid modules reflect our ongoing commitment to simplifying high-power system design," said **Manish Shah, Chief Technology Officer at TagoreTech**. "We're leveraging the unique properties of wide bandgap semiconductors to achieve superior switching performance, noise figure, and integration density—all critical to today's RF front-end architectures."

Leveraging the advantages of wide bandgap technologies, Tagore's proprietary solutions help reduce system complexity, size, and power consumption across a broad range of applications—from 5G infrastructure to consumer electronics, automotive, defense, and public safety systems.



In line with this theme, Manish Shah will present at **WMG-5:** *GaN-Si-Based RF Switch to Improve SWaP and Reduce Complexity Out of High-Power Radio Design* on June 16, 2025, at 10:40 AM (local time), **location 215.**

TagoreTech will be exhibiting at IMS 2025 from June 16–19, 2025, booth #332. For more information, visit <u>www.tagoretech.com</u>.

About TagoreTech

Founded in January 2011, TagoreTech is pioneering the use of Gallium Nitride-on-Silicon (GaN-on-Si) semiconductor technology for RF and power management applications. We are a fabless semiconductor company with design centers in Arlington Heights, Illinois, USA, and Kolkata, India. Our R&D team is focused on delivering disruptive solutions that leverage wide bandgap technologies to address RF and power design challenges, helping customers accelerate time-to-market across a wide range of applications. For more information, visit www.tagoretech.com.

For further information please contact:

Name: Anindita Ray Email: <u>ray0521@tagoretech.com</u>